N-Channel Silicon MOSFET



MCH3406

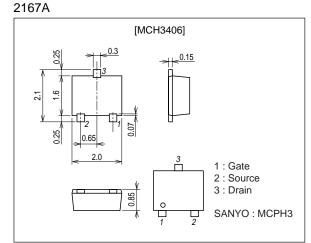
Ultrahigh-Speed Switching Applications

Features

- Low ON-state resistance.
- Ultrahigh-speed switching.
- 1.8V drive.

Package Dimensions

unit : mm



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		20	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	۱D		3	A
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	12	А
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm ² X0.8mm)	1	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	20			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0			1	μA
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VDS=0			±10	μA
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	0.4		1.3	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =1.5A	3.9	5.6		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	ID=1.5A, VGS=4V		48	63	mΩ
	RDS(on)2	ID=1A, VGS=2.5V		58	82	mΩ
	R _{DS} (on)3	I _D =0.5A, V _{GS} =1.8V		72	110	mΩ

Marking : KF

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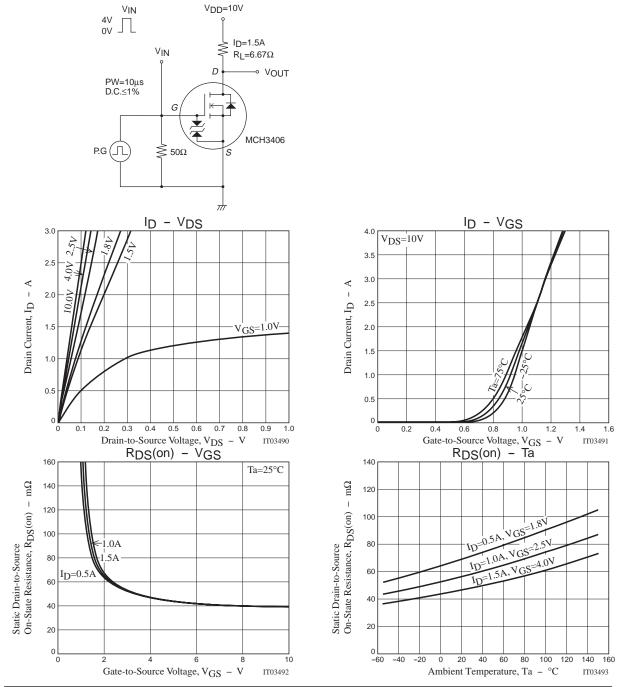
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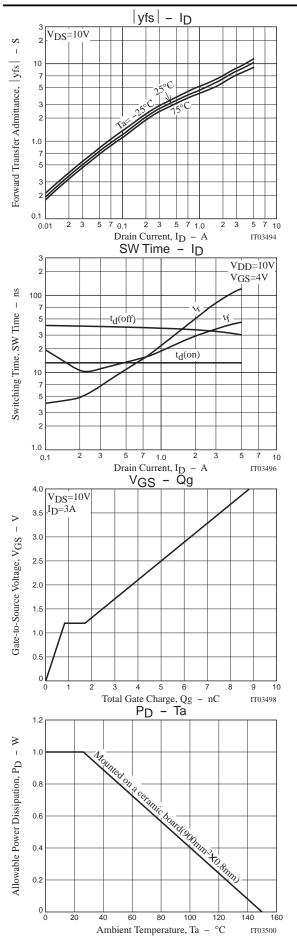
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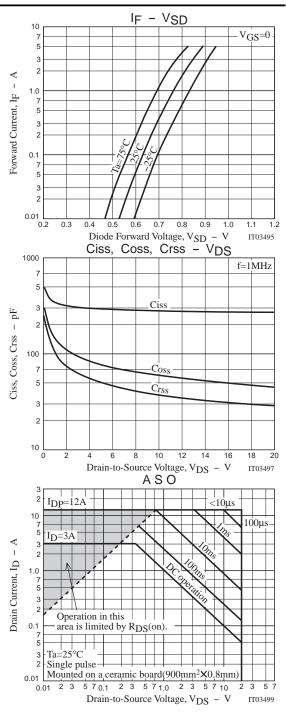
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Input Capacitance	Ciss	VDS=10V, f=1MHz		280		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		60		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		38		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit		13		ns
Rise Time	tr	See specified Test Circuit		35		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		35		ns
Fall Time	tf	See specified Test Circuit		25		ns
Total Gate Charge	Qg	VDS=10V, VGS=4V, ID=3A		8.8		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =4V, I _D =3A		0.85		nC
Gate-to-Drain "Miller" Charge	Qgd	VDS=10V, VGS=4V, ID=3A		0.85		nC
Diode Forward Voltage	V _{SD}	IS=3A, VGS=0		0.82	1.2	V

Switching Time Test Circuit



No.7010-2/4





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